Amendments to the Specification:

Please replace paragraph **[0029]** with the following amended paragraph:

[0029] In the liquid crystal display described with respect to FIG. 4, an active layer of, e.g., amorphous silicon (a-Sh:H) material, on a lower layer of pixels controlled by the number one scanning line or gate line (G1) (see FIG. 2) serves to restrict a transmission of light to pixel electrodes and to restrict the line light phenomenon. Accordingly, this active layer may also be referred to as a light transmission restricting layer.

Please replace paragraph **[0033]** with the following amended paragraph:

[0033] A gate insulating film 52 is formed on a substrate 51, a first active layer, which is a channel layer of the TFT, (not shown) is formed on the gate insulating film 52, and a ~~second active~~ light transmission restricting layer 53 is formed on the gate insulating film corresponding to a portion where the pixel electrodes are formed. Here, the first and second active layers are preferably made of amorphous silicon (a-Sh:H) material. First and second data lines 54 and 55 are patterned at right and left portions of the ~~second active~~ light transmission restricting layer 53, and a passivation layer 56 of insulating film material is formed on the substrate 51 including the data lines. A plurality of pixel electrodes 57 are patterned on the passivation layer 56 corresponding to the ~~active~~ light transmission restricting layer 53.

Please replace paragraph **[0034]** with the following amended paragraph:

[0034] The ~~second active~~ light transmission restricting layer 53 can change the thickness according to a transmission of light. When the active layer is patterned, the thickness of the ~~second active~~ light transmission restricting layer 53 can be changed by adjusting an etching speed during an etching process after a photolithography process. Moreover, also an area of the active layer can be adjusted using the photolithography process.

Please replace paragraph **[0037]** with the following amended paragraph:

[0037] As shown in FIG. 5b, the ~~active~~ light transmission restricting layer 53 of the amorphous silicon (a-Sh:H) material is evaporated on the gate insulating film 52 using the PECVD method, and then patterned through a photolithography process, an etching process and a strip process. Beneficially, the ~~active~~ light transmission restricting layer 53 is the same as the amorphous silicon layer, which is a channel layer of the TFT, and thereby the active layer is formed when the channel layer of the TFT is formed, without any additional process.

Please replace paragraph **[0038]** with the following amended paragraph:

[0038] As shown in FIG. 5c, conductive metals disposed at both sides of the ~~active~~ light transmission restricting layer 53 are evaporated using a sputtering method, and then, patterned to form data lines 54 and 55.

Please replace paragraph **[0039]** with the following amended paragraph:

[0039] As shown in FIG. 5d, the passivation layer 56 of insulating material is formed on the whole surface of the substrate 51 including the ~~active~~ light transmission restricting layer 53 and the data lines 54 and 55. A transparent conductive film of, e.g., Indium Tin Oxide (ITO) material, is evaporated on the passivation layer 56 corresponding to the active layer using the sputtering method, and then, patterned to form the pixel electrodes 57.

Please replace paragraph **[0042]** with the following amended paragraph:

[0042] When the pixel electrode controlled by the number 1 gate line (G1) is formed, the ~~active~~ light transmission restricting layer is formed on a lower layer of the pixel electrode to restrict the transmission of light, thereby preventing the light phenomenon of the number 1 gate line (G1) due to the number Ø gate line (GØ) (see FIG. 2), to which only V_{gl} signal, of the V_{gh} and V_{gl} signals, is applied.

Please replace paragraph **[0043]** with the following amended paragraph:

[0043] Furthermore, when the channel layer of the TFT is formed, the active layer is formed without requiring additional process, thereby changing the thickness and the area of the active layer through the existing process.